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SEMICONDUCTOR®

November 2013

FQP30N06L

N-Channel QFET[®] MOSFET 60 V, 32 A, 35 m Ω

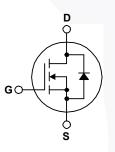
Description

This N-Channel enhancement mode power MOSFET is produced using Fairchild Semiconductor's proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state resistance, and to provide superior switching performance and high avalanche energy strength. These devices are suitable for switched mode power supplies, audio amplifier, DC motor control, and variable switching power applications.

Features

- 32 A, 60 V, $R_{DS(on)}$ = 35 m Ω (Max.) @ V_{GS} = 10 V, I_D = 16 A
- Low Gate Charge (Typ. 15 nC)
- Low Crss (Typ. 50 pF)
- 100% Avalanche Tested
- 175°C Maximum Junction Temperature Rating





Absolute Maximum Ratings T_c = 25°C unless otherwise noted.

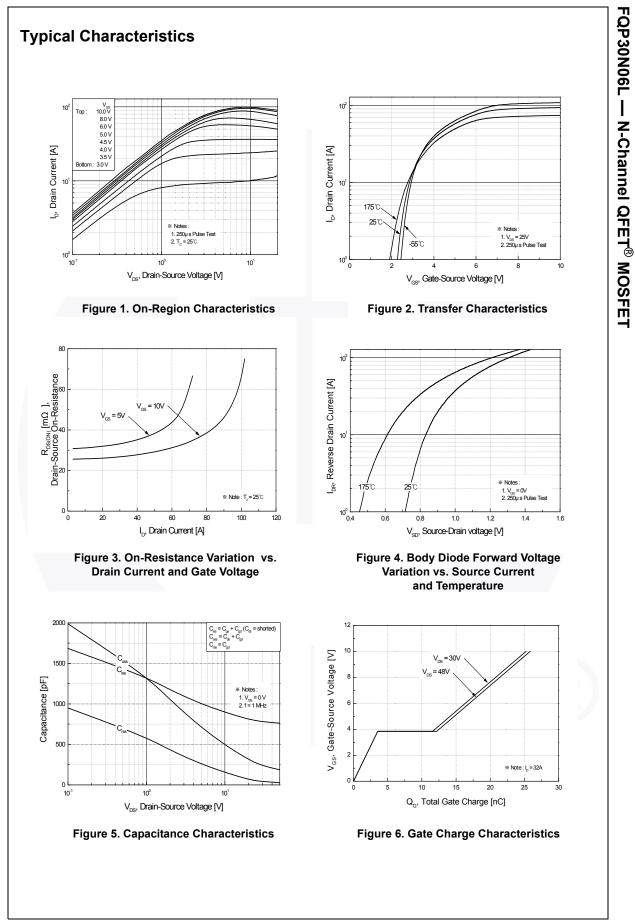
| Symbol | Parameter | | FQP30N06L | Unit |
|-----------------------------------|---|----------|-------------|------|
| V _{DSS} | Drain-Source Voltage | | 60 | V |
| I _D | Drain Current - Continuous ($T_C = 25^\circ$ | C) | 32 | A |
| | - Continuous (T _C = 100 | °C) | 22.6 | Α |
| I _{DM} | Drain Current - Pulsed | (Note 1) | 128 | Α |
| V _{GSS} | Gate-Source Voltage | | ± 20 | V |
| E _{AS} | Single Pulsed Avalanche Energy | (Note 2) | 350 | mJ |
| I _{AR} | Avalanche Current | (Note 1) | 32 | A |
| E _{AR} | Repetitive Avalanche Energy | (Note 1) | 7.9 | mJ |
| dv/dt | Peak Diode Recovery dv/dt | (Note 3) | 7.0 | V/ns |
| P _D | Power Dissipation ($T_C = 25^{\circ}C$) | | 79 | W |
| | - Derate above 25°C | | 0.53 | W/°C |
| T _J , T _{STG} | Operating and Storage Temperature Range | | -55 to +175 | °C |
| TL | Maximum Lead Temperature for Soldering, 1/8" from Case for 5 seconds | | 300 | °C |

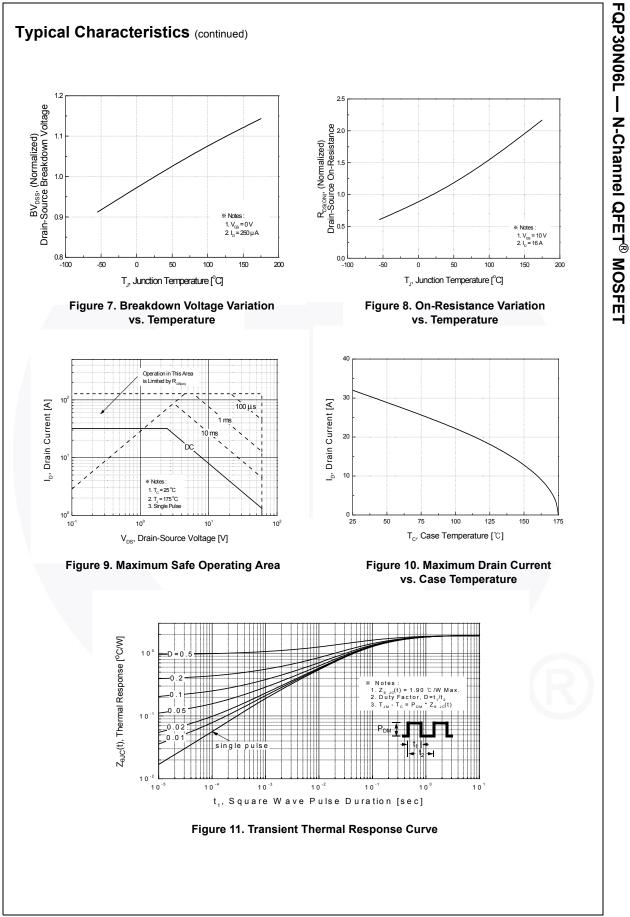
Thermal Characteristics

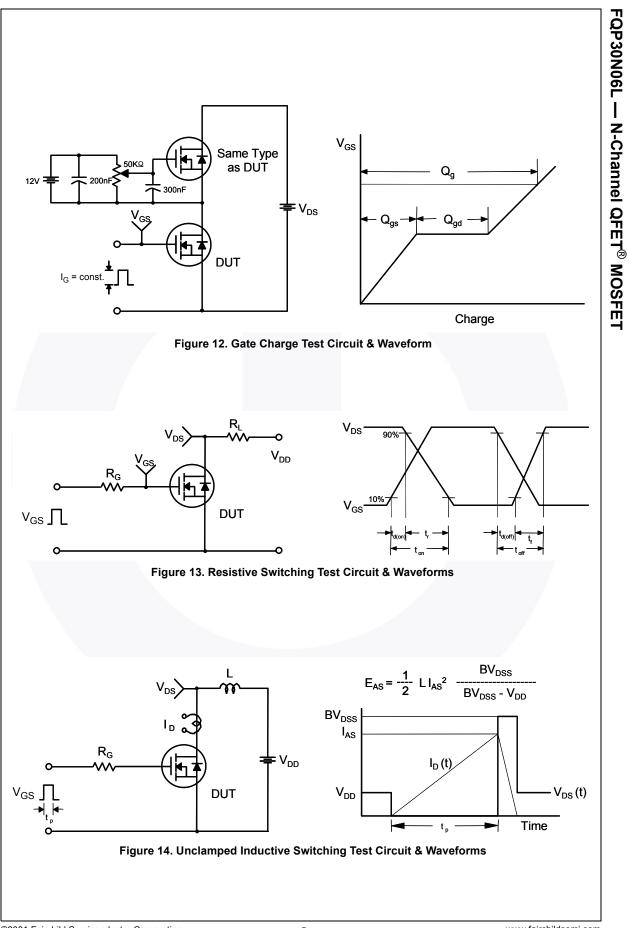
| Symbol | Parameter | FQP30N06L | Unit |
|-----------------|---|-----------|------|
| $R_{\theta JC}$ | Thermal Resistance, Junction-to-Case, Max. | 1.90 | °C/W |
| R_{\thetaJA} | Thermal Resistance, Junction-to-Ambient, Max. | 62.5 | °C/W |

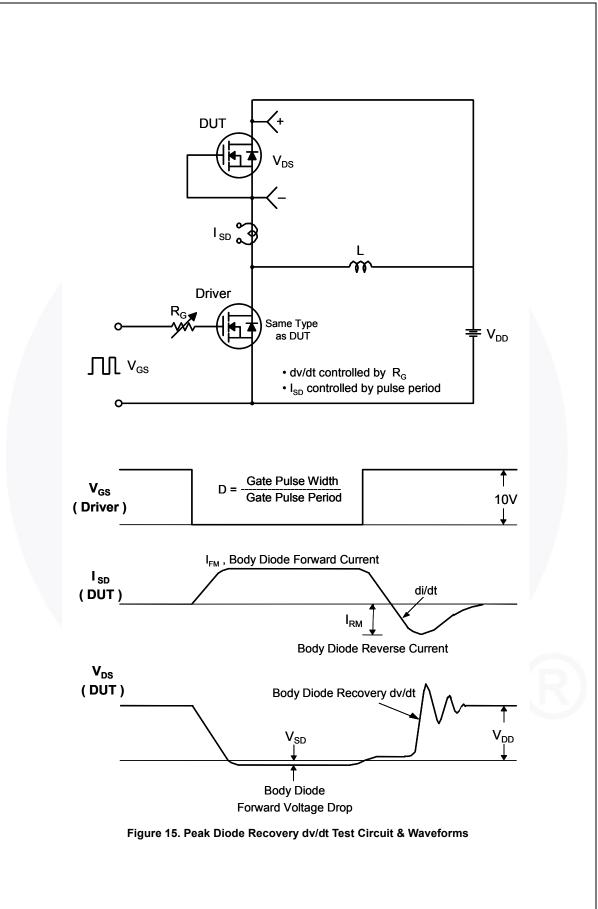
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| shold Voltage | | | | | | | |
| | | | | | | | |
| in-Source | | V_{DS} = V_{GS} , I_D = 250 μ | A | 1.0 | | 2.5 | V |
| ance | | $V_{GS} = 10 \text{ V}, I_D = 16 \text{ A}$ $V_{GS} = 5 \text{ V}, I_D = 16 \text{ A}$ | | | 0.027 0.035 | 0.035 0.045 | Ω |
| ransconductance | | V _{DS} = 25 V, I _D = 16 A | | | 24 | | S |
| acitance apacitance | nce | V _{DS} = 25 V, V _{GS} = 0 V f = 1.0 MHz | , | | 800 270 50 | 1040 350 65 | pF pF pF |
| acteristics | | | | | | | |
| | | | | | 15 | 40 | ns |
| , | | | | | 210 | 430 | ns |
| Delay Time | | $R_{G} = 25 \Omega$ | | | 60 | 130 | ns |
| 2 | | | (Note 4) | | 110 | 230 | ns |
| e Charge | | V _{DS} = 48 V I _D = 32 A | | | 15 | 20 | nC |
| | | | | | 3.5 | | nC |
| n Charge | | | (Note 4) | | 8.5 | | nC |
| | acteristics Delay Time Rise Time Delay Time Fall Time to Charge rce Charge | acitance apacitance apacitance apacitance apacitance acteristics a | vacitance $V_{DS} = 25 \text{ V}, V_{GS} = 0 \text{ V}$ apacitancef = 1.0 MHzTransfer Capacitancef = 1.0 MHzacteristics $V_{DD} = 30 \text{ V}, I_D = 16 \text{ A},$ Delay Time $V_{DD} = 30 \text{ V}, I_D = 16 \text{ A},$ Delay Time $V_{DS} = 25 \Omega$ Fall Time $V_{DS} = 48 \text{ V}, I_D = 32 \text{ A},$ rce Charge $V_{GS} = 5 \text{ V}$ | vacitance $V_{DS} = 25 \text{ V}, V_{GS} = 0 \text{ V},$ f = 1.0 MHzransfer Capacitancef = 1.0 MHzacteristics $V_{DD} = 30 \text{ V}, I_D = 16 \text{ A},$ Rise TimeDelay Time $V_{DD} = 30 \text{ V}, I_D = 16 \text{ A},$ RG = 25 Ω Tall Time $V_{DS} = 48 \text{ V}, I_D = 32 \text{ A},$ rce ChargeVois 40 Vois 5 V | acitance $V_{DS} = 25 \text{ V}, V_{GS} = 0 \text{ V},$ f = 1.0 MHzapacitancef = 1.0 MHzTransfer CapacitanceacteristicsDelay Time $V_{DD} = 30 \text{ V}, I_D = 16 \text{ A},$ $R_G = 25 \Omega$ Delay TimeFall Time(Note 4)Charge $V_{DS} = 48 \text{ V}, I_D = 32 \text{ A},$ $V_{GS} = 5 \text{ V}$ | vacitance $V_{DS} = 25 \text{ V}, V_{GS} = 0 \text{ V},$ 800 apacitance f = 1.0 MHz 270 Transfer Capacitance 50 acteristics Delay Time $V_{DD} = 30 \text{ V}, \text{ I}_D = 16 \text{ A},$ 15 Rise Time $R_G = 25 \Omega$ 60 Fall Time (Note 4) 110 e Charge $V_{DS} = 48 \text{ V}, \text{ I}_D = 32 \text{ A},$ 15 rce Charge $V_{GS} = 5 \text{ V}$ 3.5 | $\begin{array}{c c c c c c c c c c c c c c c c c c c $ |

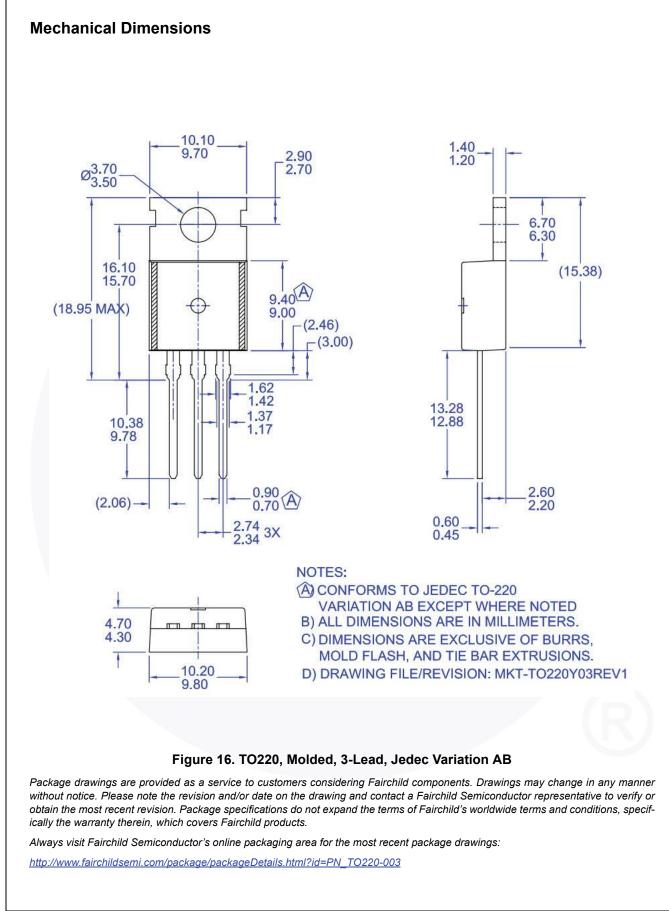
2. L = 400 µm ₁g = 52 × $_{VDP}$ = 25 × $_{SI}$ starting T = 25 °C. 3. I_{SD} = 32 Å, didt ≤ 300 Å/us, V_{DD} ≤ BV_{DSS} starting T_J = 25 °C. 4.Essentially independent of operating temperature. FQP30N06L — N-Channel QFET[®] MOSFET













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